IN THE CLAIMS

1. (Currently Amended) An inspection object silicon wafer for the purpose of detecting crystal defects characterized in that epitaxial growth is made on [[the]] a surface of a mirror surface wafer from which [[the]] a natural oxide film is removed [[of]] without surface defects being eliminated to make the crystal defects having pits and projections appear on [[the]] a surface of [[the]] an epitaxial layer.

2. (Currently Amended) An inspection object silicon wafer for the purpose of detecting crystal defects manufactured through a process of heat treatment in which [[the]] a natural oxide film is removed without eliminating [[the]] surface defects of a mirror surface wafer ~~being eliminated~~ and a process of epitaxial growth in which epitaxial growth is made on [[the]] a surface of the mirror surface wafer and the crystal defects are generated as defects having pits and projections ~~projection~~ on [[the]] a surface of the epitaxial layer.

3. (Currently Amended) An inspection object silicon wafer for the purpose of detecting crystal defects according to claim 2, ~~characterized in that~~ wherein the heat treatment process and epitaxial growth ~~deposition~~ process are performed under a hydrogen atmosphere of normal pressure at a temperature ~~temperatures conditions of~~ between 900 °C and 1080 °C.

4. (Currently Amended) A method of detecting crystal defects of a silicon wafer characterized ~~in that;~~ by:

making epitaxial growth on the surface of the silicon wafer heat-treated in a temperature condition in which the natural oxide film is removed but the surface state of the silicon wafer is preserved, wherein crystal defects having pits

and projections are made to appear on the surface of [[the]] an epitaxial layer; and

detecting the crystal defects having pits and projections ~~are detected~~ by a light scattering particle inspection apparatus.

5. (Currently Amended) A method of detecting crystal defects of a silicon wafer according to claim 4, ~~characterized in that,~~ wherein the heat treatment and the growth of epitaxial layer are performed under a hydrogen atmosphere of normal pressure ~~ordinary atmosphere~~ at a temperature between 900 °C and 1080 °C.